



UTRON

Rev. 1.5

128K X 8 BIT LOW POWER CMOS SRAM

GENERAL DESCRIPTION

FEATURES

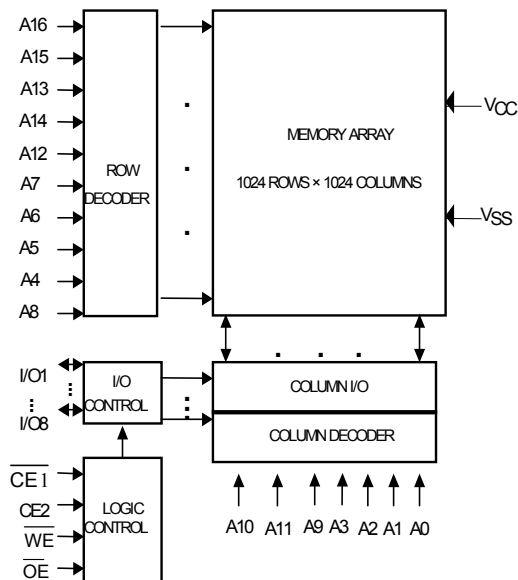
- Access time : 35/55/70ns (max.)
- Low power consumption :
Operating : 60/50/40 mA (typical)
Standby : 2μA (typical) L-version
1μA (typical) LL-version
- Single 5V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 2V (min.)
- Package : 32-pin 600 mil PDIP
32-pin 450 mil SOP
32-pin 8mmx20mm TSOP-1
32-pin 8mmx13.4mm STSOP

The UT621024 is a 1,048,576-bit low power CMOS static random access memory organized as 131,072 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

The UT621024 is designed for low power application. It is particularly well suited for battery back-up nonvolatile memory application.

The UT621024 operates from a single 5V power supply and all inputs and outputs are fully TTL compatible.

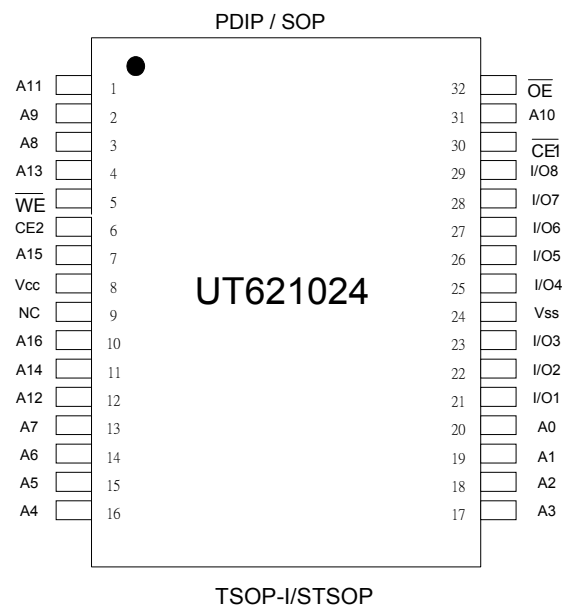
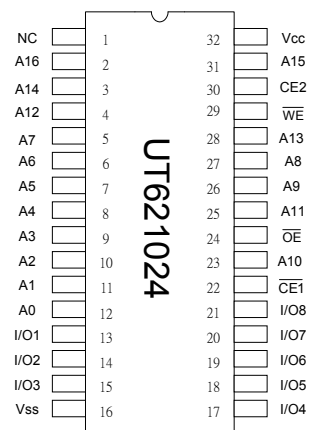
FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A16	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
CE1, CE2	Chip enable 1,2 Inputs
WE	Write Enable Input
OE	Output Enable Input
V _{CC}	Power Supply
V _{SS}	Ground
NC	No Connection

PIN CONFIGURATION



**ABSOLUTE MAXIMUM RATINGS***

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V _{SS}	V _{TERM}	-0.5 to +7.0	V
Operating Temperature	T _A	0 to +70	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA
Soldering Temperature (under 10 sec)	T _{solder}	260	°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE1	CE2	OE	WE	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	X	High - Z	I _{SB} , I _{SB1}
Standby	X	L	X	X	High -Z	I _{SB} , I _{SB1}
Output Disable	L	H	H	H	High - Z	I _{CC}
Read	L	H	L	H	D _{OUT}	I _{CC}
Write	L	H	X	L	D _{IN}	I _{CC}

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V± 10%, T_A = 0°C to 70°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input High Voltage	V _{IH}		2.2	-	V _{CC} +0.5	V
Input Low Voltage	V _{IL}		- 0.5	-	0.8	V
Input Leakage Current	I _{IL}	V _{SS} ≤ V _{IN} ≤ V _{CC}	- 1	-	1	μA
Output Leakage Current	I _{OL}	V _{SS} ≤ V _{I/O} ≤ V _{CC} CE1 = V _{IH} or CE2 = V _{IL} or OE = V _{IH} or WE = V _{IL}	- 1	-	1	μA
Output High Voltage	V _{OH}	I _{OH} = - 1mA	2.4	-	-	V
Output Low Voltage	V _{OL}	I _{OL} = 4mA	-	-	0.4	V
Average Operating Power Supply Current	I _{CC}	Cycle time=min, 100% duty, CE1 = V _{IL} , CE2 = V _{IH} , I _{I/O} = 0mA	-35	-	60	mA
			-55	-	50	mA
			-70	-	40	mA
	I _{CC1}	Cycle time=1μs, 100% duty, I _{I/O} =0mA CE1 ≤ 0.2V, CE2 ≥ V _{CC} -0.2V, other pins at 0.2V or V _{CC} -0.2V,	-	-	10	mA
Standby Power Supply Current	I _{SB}	CE1 = V _{IH} or CE2 = V _{IL} other pins at 0.2V or V _{CC} -0.2V,	-	-	3	mA
			-	-	-	-
	I _{SB1}	CE1 ≥ V _{CC} -0.2V or CE2 ≤ 0.2V other pins at 0.2V or V _{CC} -0.2V,	- L	-	2	100 40*
			- LL	-	1	50 15*

*Those parameters are for reference only under 50°C

**CAPACITANCE** ($T_A=25^{\circ}\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C_{IN}	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L=100\text{pF}$, $I_{OH}/I_{OL}=-1\text{mA}/4\text{mA}$

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_A = 0^{\circ}\text{C}$ to 70°C)**(1) READ CYCLE**

PARAMETER	SYMBOL	UT621024-35		UT621024-55		UT621024-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	35	-	55	-	70	-	ns
Address Access Time	t_{AA}	-	35	-	55	-	70	ns
Chip Enable Access Time	t_{ACE1} , t_{ACE2}	-	35	-	55	-	70	ns
Output Enable Access Time	t_{OE}	-	25	-	30	-	35	ns
Chip Enable to Output in Low-Z	t_{CLZ1}^* , t_{CLZ2}^*	10	-	10	-	10	-	ns
Output Enable to Output in Low-Z	t_{OLZ}^*	5	-	5	-	5	-	ns
Chip Disable to Output in High-Z	t_{CHZ1}^* , t_{CHZ2}^*	-	25	-	30	-	35	ns
Output Disable to Output in High-Z	t_{OHZ}^*	-	25	-	30	-	35	ns
Output Hold from Address Change	t_{OH}	5	-	5	-	5	-	ns

(2) WRITE CYCLE

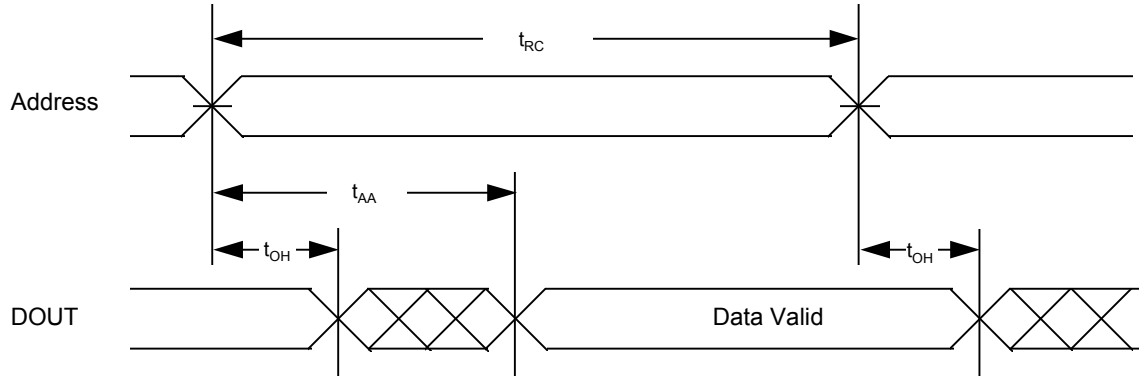
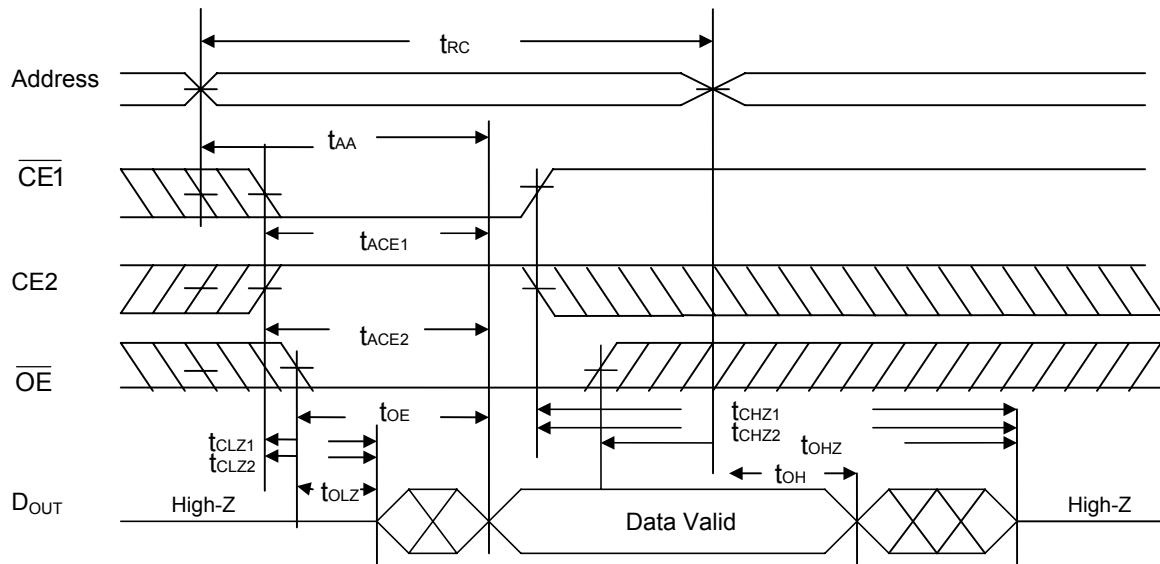
PARAMETER	SYMBOL	UT621024-35		UT621024-55		UT621024-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	35	-	55	-	70	-	ns
Address Valid to End of Write	t_{AW}	30	-	50	-	60	-	ns
Chip Enable to End of Write	t_{CW1} , t_{CW2}	30	-	50	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	25	-	40	-	45	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	20	-	25	-	30	-	ns
Data Hold from End of Write-Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW}^*	5	-	5	-	5	-	ns
Write to Output in High-Z	t_{WHZ}^*	-	15	-	20	-	25	ns

*These parameters are guaranteed by device characterization, but not production tested.



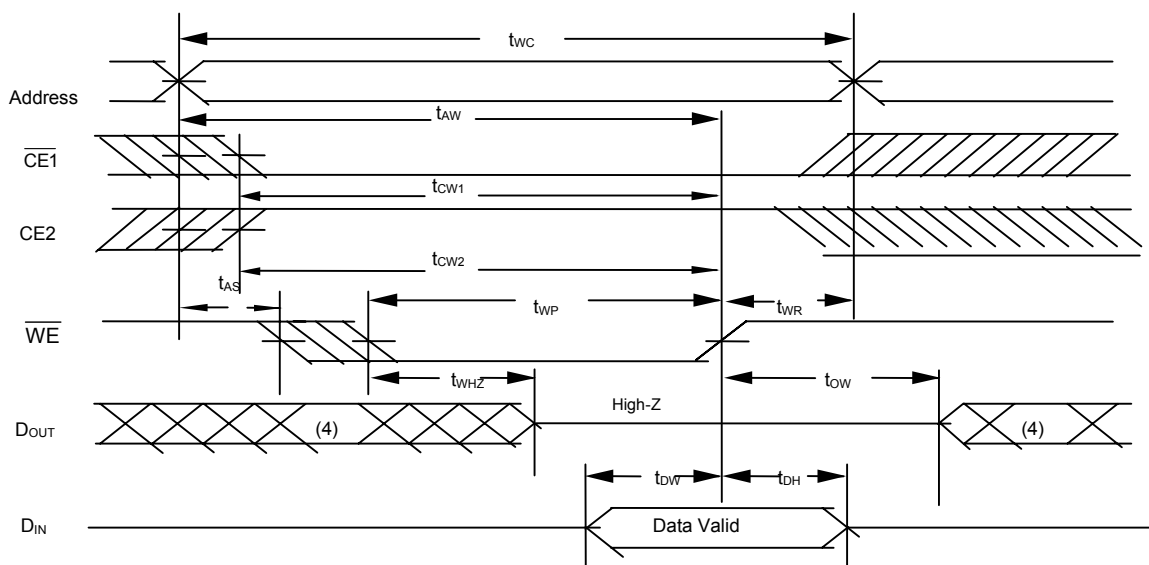
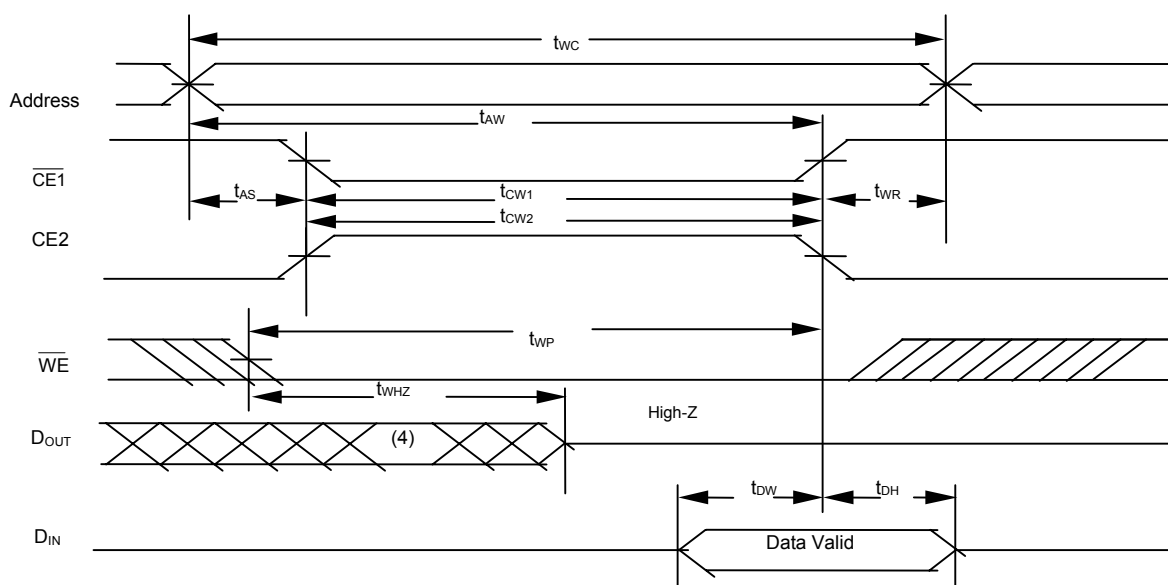
TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2,4)

READ CYCLE 2 ($\overline{CE1}$, CE2 and $\overline{OE}$ Controlled) (1,3,5,6)

Notes :

1. $\overline{WE}$ is HIGH for read cycle.
2. Device is continuously selected $\overline{CE1}=V_{IL}$ and $CE2=V_{IH}$.
3. Address must be valid prior to or coincident with $\overline{CE1}$ and CE2 transition; otherwise t_{AA} is the limiting parameter.
4. $\overline{OE}$ is low.
5. t_{CLZ1} , t_{CLZ2} , t_{OLZ} , t_{CHZ1} , t_{CHZ2} and t_{OHZ} are specified with $C_L=5pF$. Transition is measured $\pm 500mV$ from steady state.
6. At any given temperature and voltage condition, t_{CHZ1} is less than t_{CLZ1} , t_{CHZ2} is less than t_{CLZ2} , t_{OHZ} is less than t_{OLZ} .

**WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5)****WRITE CYCLE 2 ($\overline{CE1}$ and CE2 Controlled) (1,2,5)****Notes :**

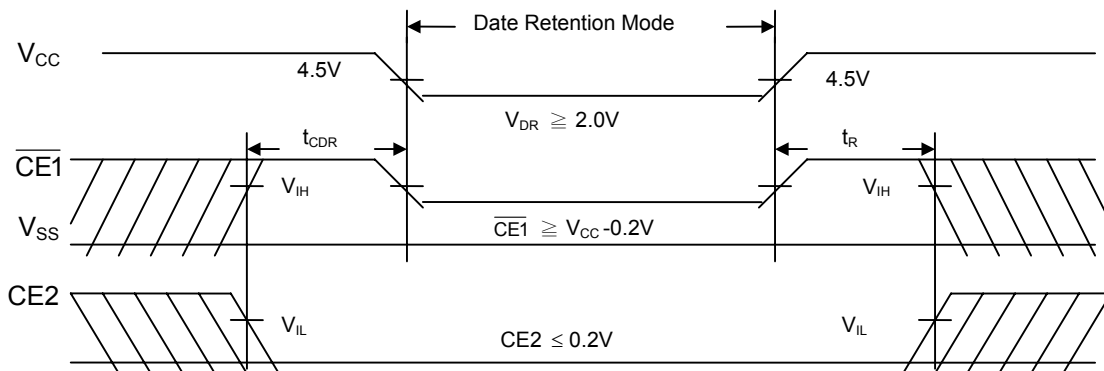
1. $\overline{WE}$ or $\overline{CE1}$ must be HIGH or CE2 must be LOW during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE1}$, a high CE2 and a low $\overline{WE}$.
3. During a $\overline{WE}$ controlled with write cycle with $\overline{OE}$ LOW, t_{WP} must be greater than $t_{WHZ} + t_{OW}$ to allow the I/O drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE1}$ LOW transition occurs simultaneously with or after $\overline{WE}$ LOW transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5\text{pF}$. Transition is measured $\pm 500\text{mV}$ from steady state.

**DATA RETENTION CHARACTERISTICS** ($T_A = 0^{\circ}\text{C}$ to 70°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _{CC} for Data Retention	V _{DR}	$\overline{\text{CE1}} \geq V_{\text{CC}} - 0.2\text{V}$ or $\text{CE2} \leq 0.2\text{V}$	2.0	-	-	V
Data Retention Current	I _{DR}	V _{CC} =3V	- L	1	40	μA
					20*	
		$\overline{\text{CE1}} \geq V_{\text{CC}} - 0.2\text{V}$ or $\text{CE2} \leq 0.2\text{V}$	- LL	0.5	20	μA
					10*	
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC} *	-	-	ns

t_{RC}* = Read Cycle Time

*Those parameters are for reference only under 50°C

DATA RETENTION WAVEFORM



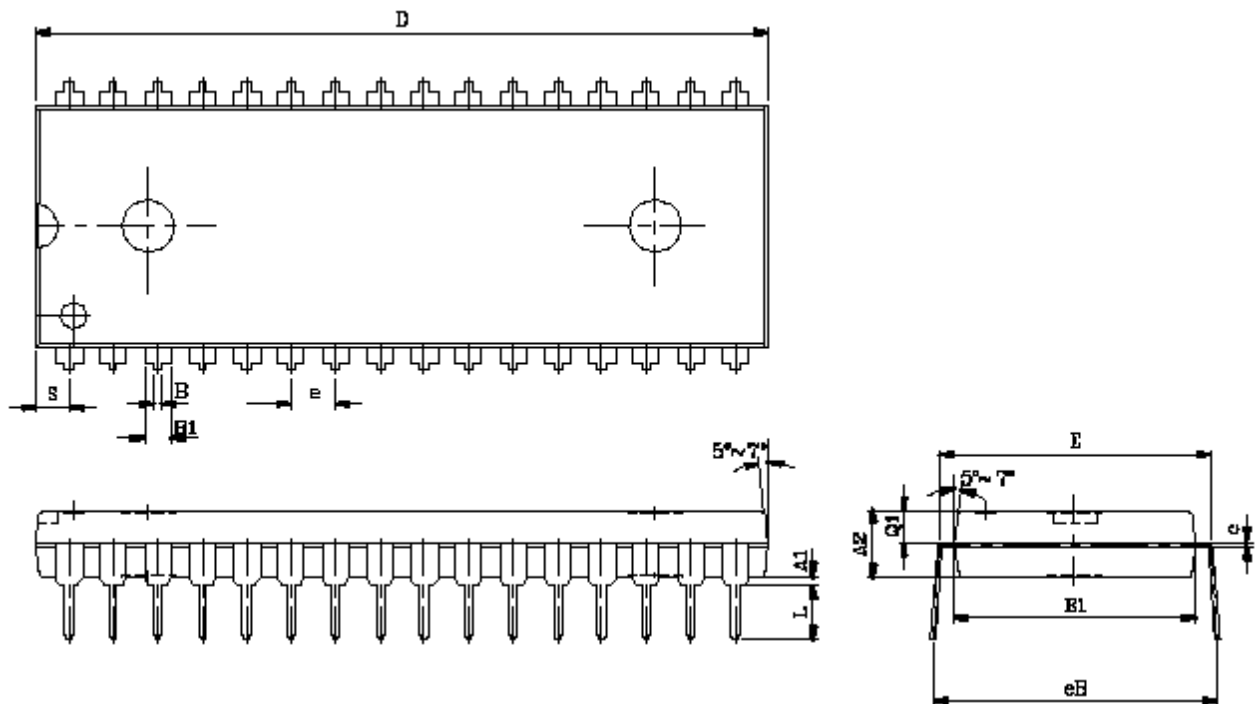
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Rev. 1.5

UT621024
128K X 8 BIT LOW POWER CMOS SRAM

PACKAGE OUTLINE DIMENSION

32 pin 600 mil PDIP Package Outline Dimension



SYMBOL	UNIT	
	INCH(BASE)	MM(REF)
A1	0.010 (MIN)	0.254 (MIN)
A2	0.150 ± 0.005	3.810 ± 0.127
B	0.018 ± 0.005	0.457 ± 0.127
B1	0.050 ± 0.005	1.270 ± 0.127
c	0.010 ± 0.004	0.254 ± 0.102
D	1.650 ± 0.005	41.910 ± 0.127
E	0.600 ± 0.010	15.240 ± 0.254
E1	0.544 ± 0.004	13.818 ± 0.102
e	0.100(TYP)	2.540(TYP)
eB	0.640 ± 0.020	16.256 ± 0.508
L	0.130 ± 0.010	3.302 ± 0.254
S	0.075 ± 0.010	1.905 ± 0.254
Q1	0.070 ± 0.005	1.778 ± 0.127

Note:

1. D/E1/S DIMENSION DO NOT INCLUDE MOLD FLASH.



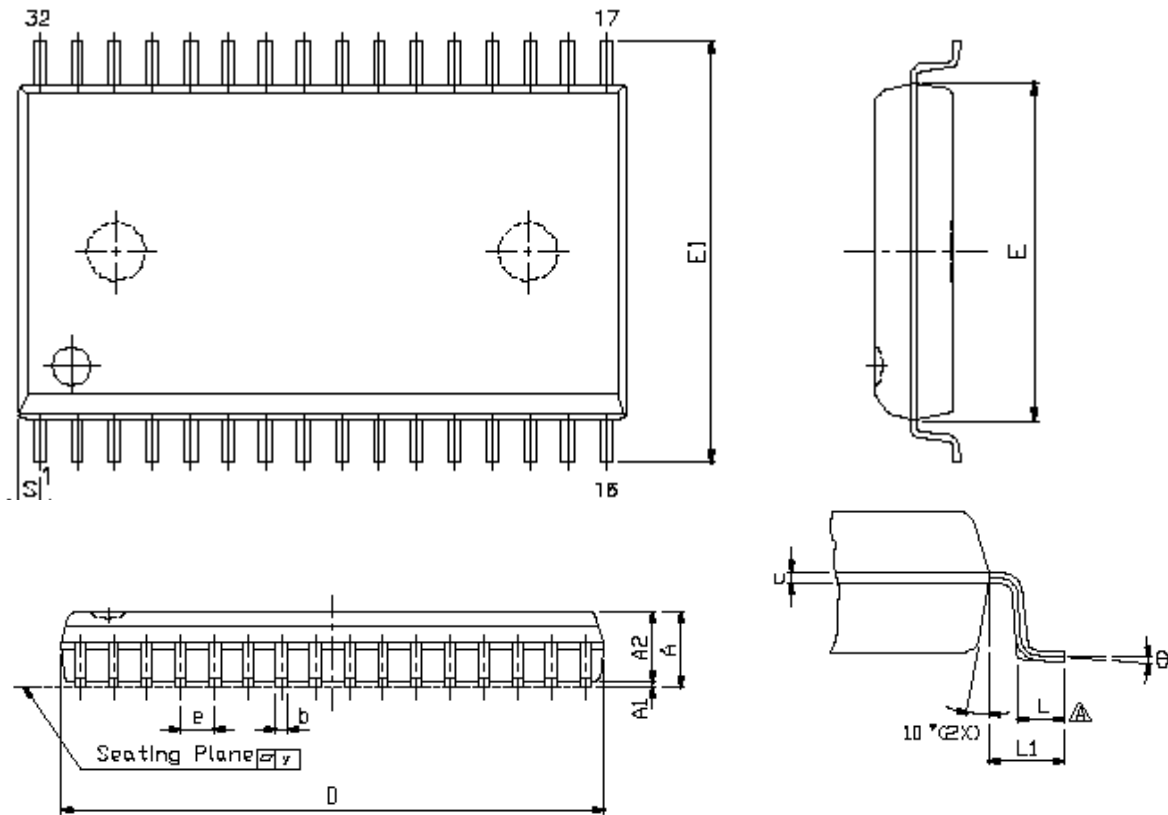
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Rev. 1.5

UT621024

128K X 8 BIT LOW POWER CMOS SRAM

32 pin 450mil SOP Package Outline Dimension



SYMBOL	UNIT	INCH(BASE)	MM(REF)
A		0.118 (MAX)	2.997 (MAX)
A1		0.004(MIN)	0.102(MIN)
A2		0.111(MAX)	2.82(MAX)
b		0.015(MIN) 0.020(MAX)	0.38(MIN) 0.50(MAX)
c		0.008(TYP)	0.203(TYP)
D		0.817(MAX)	20.75(MAX)
E		0.445 ± 0.005	11.303 ± 0.127
E1		0.555 ± 0.005	14.097 ± 0.127
e		0.050(TYP)	1.270(TYP)
L		0.0347 ± 0.008	0.881 ± 0.203
L1		0.055 ± 0.008	1.397 ± 0.203
S		0.026(MAX)	0.660 (MAX)
y		0.004(MAX)	0.101(MAX)
Θ		0° -10°	0° -10°



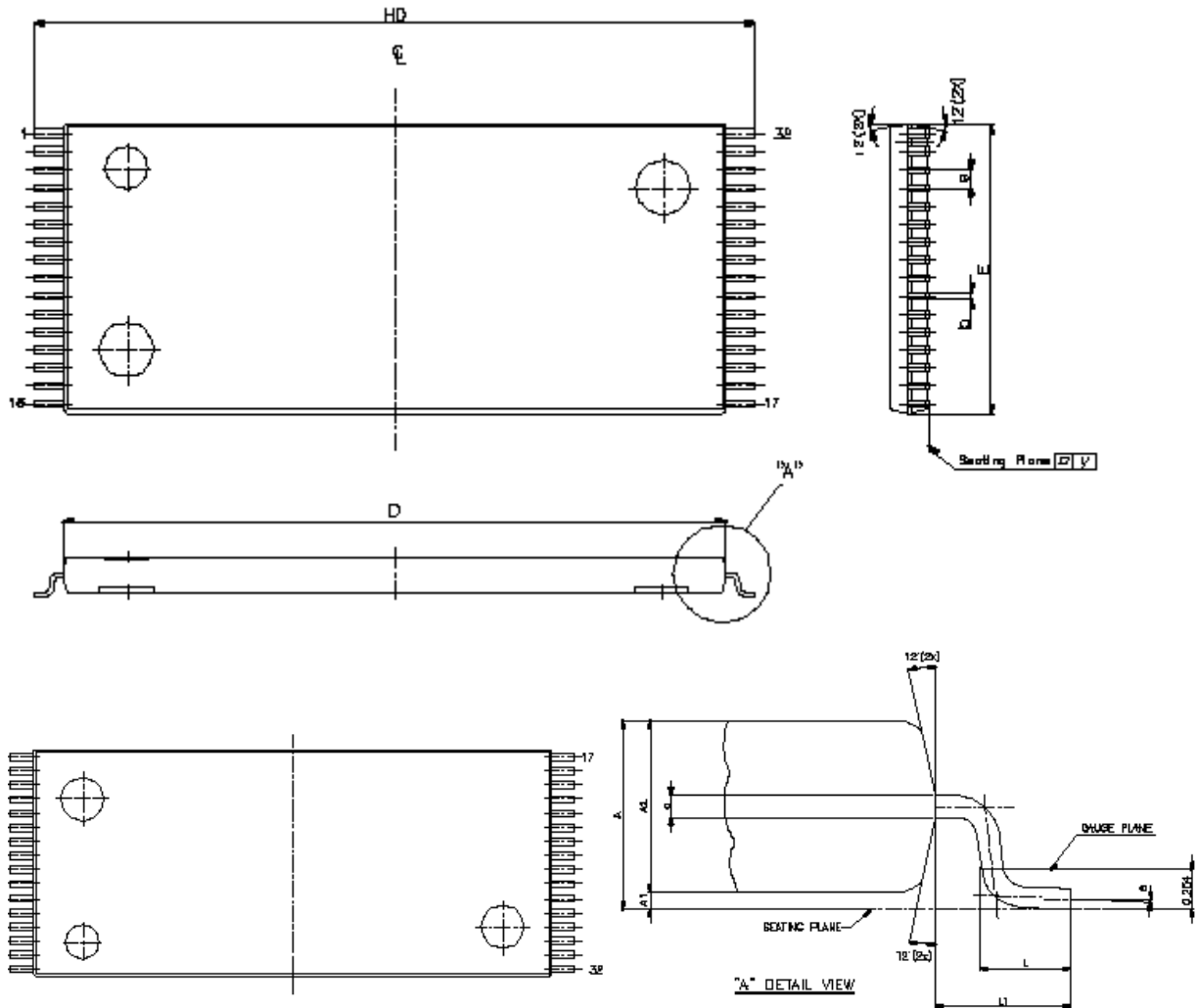
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Rev. 1.5

UT621024

128K X 8 BIT LOW POWER CMOS SRAM

32 pin TSOP-I Package Outline Dimension



SYMBOL	UNIT	
	INCH(BASE)	MM(REF)
$\triangle_C$ A	0.047 (MAX)	1.20 (MAX)
$\triangle_C$ A1	0.004 ± 0.002	0.10 ± 0.05
$\triangle_C$ A2	0.039 ± 0.002	1.00 ± 0.05
$\triangle_E$ b	$0.008 + 0.002$ $- 0.001$	$0.20 + 0.05$ $- 0.03$
c	0.005 (TYP)	0.127 (TYP)
D	0.724 ± 0.004	18.40 ± 0.10
E	0.315 ± 0.004	8.00 ± 0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.787 ± 0.008	20.00 ± 0.20
L	0.0197 ± 0.004	0.50 ± 0.10
L1	0.0315 ± 0.004	0.08 ± 0.10
$\triangle_H$ y	0.003 (MAX)	0.076 (MAX)
$\triangle_B$ θ	$0^\circ \sim 5^\circ$	$0^\circ \sim 5^\circ$



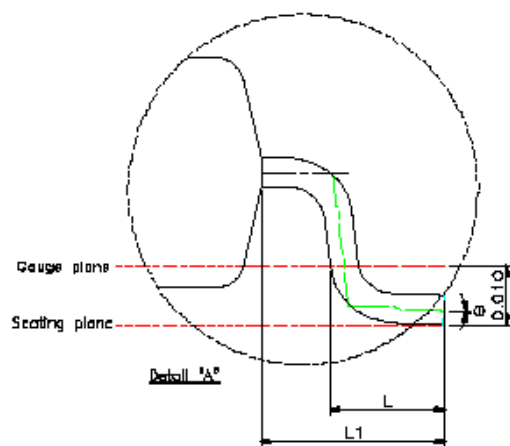
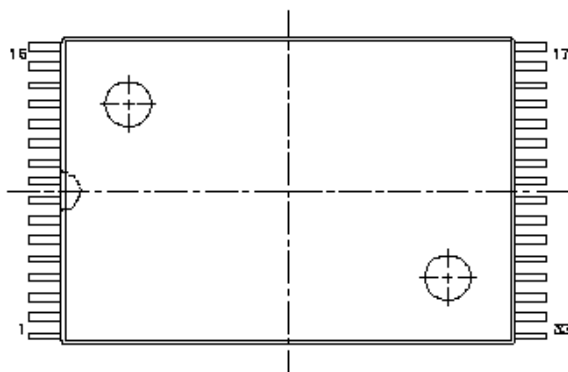
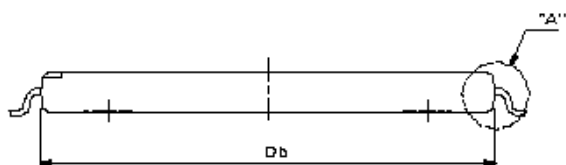
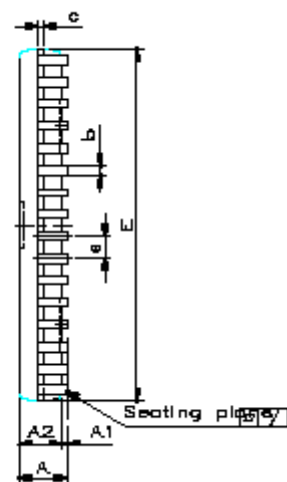
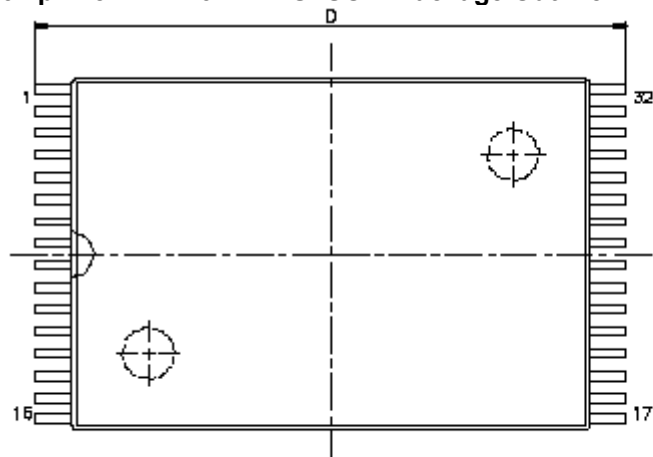
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UT621024

Rev. 1.5

128K X 8 BIT LOW POWER CMOS SRAM

32 pin 8mm x 13.4mm STSOP Package Outline Dimension



t Symbol	Uni	MM(REF)	INCH(BASE)
A		1.20(Max.)	0.047(Max.)
A1		0.10 ± 0.05	0.004 ± 0.002
A2		1.00 ± 0.05	0.039 ± 0.002
b		0.20(TYP.)	0.006(TYP.)
c		0.15(TYP.)	0.006(TYP.)
D		13.40 ± 0.20	0.526 ± 0.006
Db		11.80 ± 0.10	0.465 ± 0.004
E		8.000 ± 0.10	0.315 ± 0.004
e		0.50(TYP.)	0.020(TYP.)
L		0.50 ± 0.10	0.020 ± 0.004
L1		0.80 ± 0.10	0.0315 ± 0.004
y		0.08(Max.)	0.003(Max.)
e		0°~5°	0°~5°

Note :

- 1.E dimension is not including end flash.
- 2.The total of both sides' end flash is not above 0.3mm.

**ORDERING INFORMATION**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μA)	PACKAGE
UT621024PC-35L	35	100	32 PIN PDIP
UT621024PC-35LL	35	50	32 PIN PDIP
UT621024SC-35L	35	100	32 PIN SOP
UT621024SC-35LL	35	50	32 PIN SOP
UT621024LC-35L	35	100	32 PIN TSOP-I
UT621024LC-35LL	35	50	32 PIN TSOP-I
UT621024LS-35L	35	100	32 PIN STSOP
UT621024LS-35LL	35	50	32 PIN STSOP
UT621024PC-55L	55	100	32 PIN PDIP
UT621024PC-55LL	55	50	32 PIN PDIP
UT621024SC-55L	55	100	32 PIN SOP
UT621024SC-55LL	55	50	32 PIN SOP
UT621024LC-55L	55	100	32 PIN TSOP-I
UT621024LC-55LL	55	50	32 PIN TSOP-I
UT621024LS-55L	55	100	32 PIN STSOP
UT621024LS-55LL	55	50	32 PIN STSOP
UT621024PC-70L	70	100	32 PIN PDIP
UT621024PC-70LL	70	50	32 PIN PDIP
UT621024SC-70L	70	100	32 PIN SOP
UT621024SC-70LL	70	50	32 PIN SOP
UT621024LC-70L	70	100	32 PIN TSOP-I
UT621024LC-70LL	70	50	32 PIN TSOP-I
UT621024LS-70L	70	100	32 PIN STSOP
UT621024LS-70LL	70	50	32 PIN STSOP



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128K X 8 BIT LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	DATE
REV. 1.0	Original.	Apr. 05 2000
REV. 1.1	NA	--
REV. 1.2	NA	--
REV. 1.3	Add STSOP-I Package	Aug. 29.2000
REV. 1.4	Modify the format of power consumption	Sep. 01.2000
REV. 1.5	1. Operating : 60/40 -> 60/50/40 2. Standby Current : 10 ->2 (L-version) 3. Add I _{CC} -data as (-55, TYP 50, MAX 85) 4. Revise I _{SB1} TYP : 10-> 2, MAX : 300/100 ->100/40 5. The symbols CE1#, OE# & WE# are revised as $\overline{CE1}$, $\overline{OE}$ & $\overline{WE}$	Jun. 18,2001



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331